

ES2ABF THRU ES2JBF

Surface Mount Superfast Recovery Rectifier

Reverse Voltage - 50 to 600 V

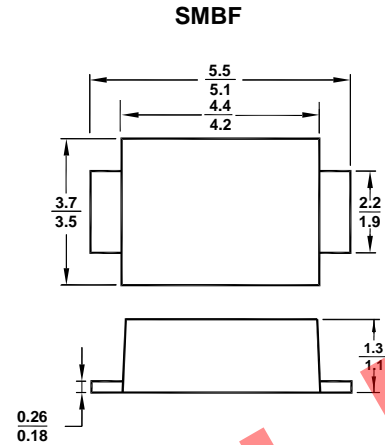
Forward Current - 2 A

Features

- Glass Passivated Chip Junction
- For surface mounted applications
- Low profile package
- Superfast reverse recovery time

Mechanical Data

- **Case:** SMBF
- **Terminals:** Solderable per MIL-STD-750, Method 2026



All Dimensions in mm

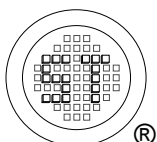
Absolute Maximum Ratings and Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbols	ES2ABF	ES2BBF	ES2CBF	ES2DBF	ES2EBF	ES2GBF	ES2JBF	Units
	Marking	E2AB	E2BB	E2CB	E2DB	E2EB	E2GB	E2JB	-
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at $T_a = 100^\circ\text{C}$	$I_{F(AV)}$	2							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	50							A
Maximum Forward Voltage at 2 A	V_F	1				1.25		1.65	V
Maximum Reverse Current at Rated DC Blocking Voltage $T_a = 25^\circ\text{C}$ $T_a = 125^\circ\text{C}$	I_R	5 100							μA
Typical Junction Capacitance at $V_R = 4\text{ V}$, $f = 1\text{ MHz}$	C_j	45							pF
Maximum Reverse Recovery Time at $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $I_{rr} = 0.25\text{ A}$	t_{rr}	35							ns
Typical Thermal Resistance ¹⁾	$R_{\theta JA}$	65							$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150							$^\circ\text{C}$

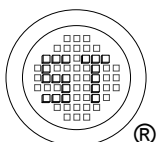
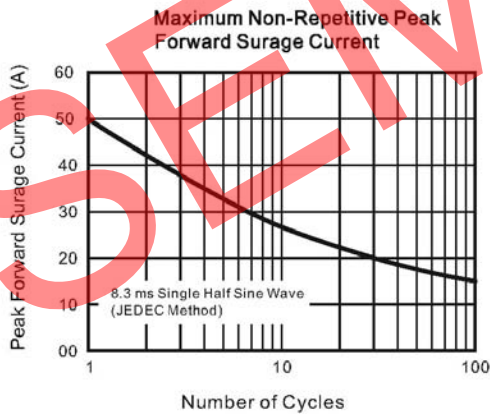
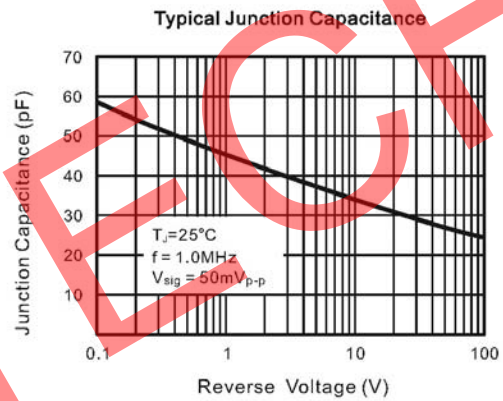
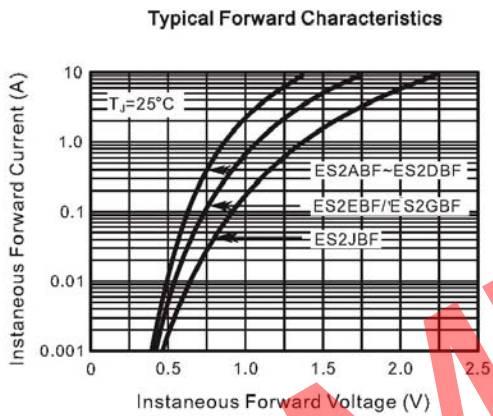
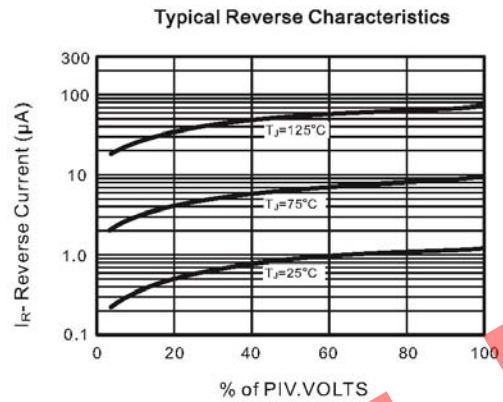
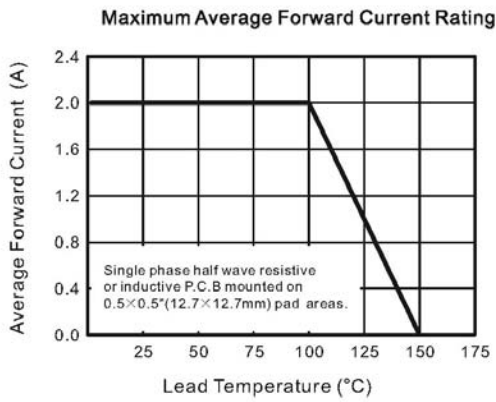
¹⁾ P.C.B. mounted with 0.5 X 0.5" (12.7 X 12.7 mm) copper pad areas.



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